ABSTRACT

A sputtering chamber system and method uses at least one sputtering source with a new sputter surface at least approximately symmetrical with respect to a central axis. A substrate carrier is arranged to be drivingly rotatable about a substrate carrier axis. The central axis and the substrate carrier axis are oblique with respect to one another, and the sputtering source is a magnetron sputtering source. The new sputter surface is substantially rotationally symmetrical with respect to the central axis, with the central axis and the substrate carrier axis intersecting at least approximately. With respect to an angle β between the central axis and the substrate carrier axis,

$$30^{\circ} \leq \beta \leq 60^{\circ}$$
,

preferably

$$40^{\circ} \leq \beta \leq 55^{\circ}$$
,

particularly preferably

$$43^{\circ} \leq \beta \leq 50^{\circ}$$
,

particularly

$$\beta \approx 45^{\circ}$$
.